WHAT IS CLAIMED IS:

1. A CVD apparatus comprising:

a chamber in which an object to be processed is mounted;

a gas outlet discharging into said chamber deposition gas to deposit a CVD film on said object to be processed;

a gas mixer connected to said gas outlet, and having a plurality of types of gases introduced and mixed to generate said deposition gas;

a plurality of gas vaporizers, configured based on a usage of a plurality of gas vaporizers to evaporate liquid source gas and generate any of said plurality of types of gases;

a plurality of source gas origins, configured based on a usage of a plurality of liquid source gas origins in which is stored said liquid source gas to be supplied to said gas vaporizer;

a plurality of gas pipes connected to said gas mixer and respective plurality of gas vaporizers, configured based on a usage of a plurality of gas pipes to guide any of said plurality of types of gases from said gas vaporizer to said gas mixer; and

a plurality of source gas pipes connecting respective said plurality of liquid source gas origins and respective said plurality of gas vaporizers;

said gas pipe and said source gas pipe corresponding to said gas pipe constituting pipes of one line, and lengths of a plurality of pipe lines are substantially identical to each other in comparison of said plurality of pipe lines with each other.

2. The CVD apparatus according to claim 1, wherein

only a gas flow rate regulating valve is substantially provided at each of said plurality of gas pipes, and

said gas vaporizer is provided at a neighborhood of said gas mixer.

3. The CVD apparatus according to claim 1, wherein

each of said plurality of gas vaporizers is connected to a flow acceleration gas pipe through which is guided flow acceleration gas

accelerating flow of said plurality of types of gases in said gas pipe, and said plurality of types of gases are introduced into said mixer in a state where said flow acceleration gas is mixed.

4. A CVD apparatus comprising:

a chamber in which an object to be processed is mounted;

a gas outlet to discharge into said chamber deposition gas to deposit a CVD film on said object to be processed;

a gas mixer connected to said gas outlet, and having a plurality of types of gases introduced and mixed to generate said deposition gas;

a deposition gas channel guiding said deposition gas from said gas mixer to said gas outlet; and

an unreaction suppression gas pipe connected to said deposition gas channel to guide unreaction suppression gas into said deposition gas channel, said unreaction suppression gas suppressing said deposition gas from being discharged out from said gas outlet in an unreacted state.

5. The CVD apparatus according to claim 4, wherein a gas flow rate control valve adjusting a flow rate of said unreaction suppression gas is provided at a neighborhood of a connection between said deposition gas channel and said unreaction suppression gas pipe.

6. A CVD apparatus comprising:

a chamber in which an object to be processed is mounted;

a gas outlet discharging into said chamber deposition gas to deposit a CVD film on said object to be processed;

a gas mixer connected to said gas outlet, and having a plurality of types of gases introduced and mixed to generate said deposition gas;

a gas vaporizer evaporating liquid source gas to generate any of said plurality of types of gases;

a gas pipe connected to said gas mixer and said gas vaporizer to guide any of said plurality of types of gases; and

a gas flow rate control mechanism provided at said gas pipe to

control a flow rate of any of said plurality of types of gases such that said deposition gas is gradually introduced into said chamber.

7. The CVD apparatus according to claim 6, wherein

said gas vaporizer is connected to a flow acceleration gas pipe through which is guided flow acceleration gas accelerating flow of said plurality of types of gases in said gas pipe, and

said plurality of types of gases are introduced into said mixer in a state where said flow acceleration gas is mixed.

8. The CVD apparatus according to claim 6, wherein said gas flow rate control mechanism comprises

a first gas flow rate regulating valve provided at said gas pipe to adjust a flow rate of gas in said gas pipe,

a discharge gas pipe connected to said gas pipe to guide gas in said gas pipe out from said chamber, and

a second gas flow rate regulating valve provided at said discharge gas pipe to adjust a flow rate of gas in said discharge gas pipe.

9. The CVD apparatus according to claim 8, wherein said gas flow rate control mechanism comprises

first flow rate control means for controlling a flow rate of gas passing through said first gas flow rate regulating valve by controlling a degree of opening up said first gas flow rate regulating valve, and

second flow rate control means for controlling a flow rate of gas passing through said second gas flow rate regulating valve by controlling a degree of opening up said second gas flow rate regulating valve.

10. The CVD apparatus according to claim 9, wherein said gas flow rate control mechanism operates said first flow rate control means to increase flow of gas passing through said first flow rate regulating valve while said second flow rate control means is operated to reduce flow of gas passing through said second flow rate regulating valve.

11. A CVD apparatus comprising:

a chamber in which an object to be processed is mounted;

a gas outlet to discharge into said chamber deposition gas to deposit a CVD film on said object to be processed;

a gas mixer connected to said gas outlet, and having a plurality of types of gases introduced and mixed to generate said deposition gas;

a gas vaporizer to evaporate liquid source gas to generate any of said plurality of types of gases;

a liquid source gas origin supplying said liquid source gas to said gas vaporizer;

a connection pipe connecting said gas vaporizer with said liquid source gas origin; and

a gas flow rate control mechanism provided at said connection pipe to control a flow rate of said liquid source gas,

said liquid source gas, said liquid source gas origin, said connection pipe, and said gas vaporizer are respectively provided in plurality, corresponding to respective said plurality of types of gases,

said gas flow rate control mechanism controlling a timing of output of said liquid source gas from respective said plurality of liquid source gas origins such that the timing of each of said plurality of types of gases being introduced into said gas mixer is substantially identical.

12. The CVD apparatus according to claim 11, wherein

said gas flow rate control mechanism comprises a sequence controller controlling a timing of introducing said deposition gas into said chamber,

a liquid source gas valve opening and closing in response to an instruction signal from said sequence controller is provided at each of said plurality of connection tubes,

said sequence controller comprises

clock means for calculating a plurality of arriving times required for each of said plurality of types of liquid source gases to arrive at said chamber from each of said plurality of types of liquid source gas origins,

calculation means for obtaining a difference in an arriving time of said plurality of types of liquid source gases based on said plurality of arriving times calculated by said clock means, and

instruction means for sequentially providing said instruction signal to each of said plurality of liquid source gas valves in accordance with the difference in the arriving time calculated by said calculation means,

each of a plurality of said liquid source gas valves receiving said instruction signal to open so as to conduct a flow of said liquid source gas at a timing specified by said instruction signal.